



DMP3036SFG

30V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

| BV _{DSS} | R _{DS(ON)} Max | I _D Max T _C = +25°C | | | |
|-------------------|------------------------------|--|--|--|--|
| -30V | $20m\Omega @ V_{GS} = -10V$ | -30A | | | |
| | 29mΩ @ V _{GS} = -5V | -30A | | | |

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

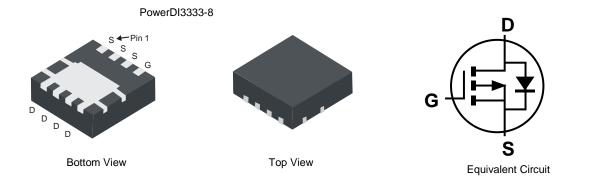
- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

Features and Benefits

- Low R_{DS(ON)} ensures on state losses are minimized.
- Small form factor thermally efficient package enables higher density end products.
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product.
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: PowerDI[®]3333-8 •
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram Terminals: Finish - Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208@3
- Weight: 0.03 grams (Approximate)



Ordering Information (Note 4)

| Part Number | Case | Packaging |
|---------------|---------------|-------------------|
| DMP3036SFG-7 | PowerDI3333-8 | 2,000/Tape & Reel |
| DMP3036SFG-13 | PowerDI3333-8 | 3,000/Tape & Reel |

Notes:

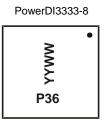
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at httphttps://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



P36 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 17 = 2017) WW = Week Code (01 to 53)

PowerDI is a registered trademark of Diodes Incorporated.



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | |
|--|--|-------|--------------|---|
| Drain-Source Voltage | V _{DSS} | -30 | V | |
| Gate-Source Voltage | V _{GSS} | ±25 | V | |
| Continuous Drain Current (Note 6) V_{GS} = -10V | T _A = +25°C T _A = +70°C | ID | -8.7 -7.0 | A |
| Continuous Drain Current (Note 7) $V_{GS} = -10V$ | T _C = +25°C T _C = +70°C | ID | -30 -25 | A |
| Continuous Drain Current (Note 6) $V_{GS} = -5V$ | T _A = +25°C T _A = +70°C | ID | -7.2 -5.8 | A |
| Continuous Drain Current (Note 7) $V_{GS} = -5V$ $T_C = +25^{\circ}C$ $T_C = +70^{\circ}C$ | | ID | -30 -24 | A |
| Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%) | I _{DM} | -80 | A | |
| Maximum Continuous Body Diode Forward Current (Note 6) | ls | -3.6 | A | |
| Avalanche Current (Note 7) L=0.3mH | I _{AS} | -17.5 | A | |
| Avalanche Energy (Note 7) L=0.3mH | E _{AS} | 64 | mJ | |

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

| Characteristic | Symbol | Value | Unit | |
|--|-------------------|-----------------------|------|------|
| Total Power Dissipation (Note 5) | | PD | 0.9 | W |
| Thermal Resistance, Junction to Ambient (Note 5) | Steady State | P | 137 | °C/W |
| Thermal Resistance, Junction to Ambient (Note 5) | t<10s | $R_{	extsf{	heta}JA}$ | 65 | °C/W |
| Total Power Dissipation (Note 6) | | PD | 2.3 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | Steady State | Р | 55 | °C/W |
| Thermal Resistance, Junction to Ambient (Note 6) | t<10s | $R_{	extsf{	heta}JA}$ | 26 | °C/W |
| Thermal Resistance, Junction to Case (Note 7) | R _θ JC | 3.5 | °C/W | |
| Operating and Storage Temperature Range | TJ. TSTG | -55 to +150 | °C | |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition | |
|--|---------------------|--------|------|------|---------|---|--|
| OFF CHARACTERISTICS (Note 8) | Symbol | IVIIII | тур | WIAX | Unit | Test condition | |
| Drain-Source Breakdown Voltage | BV _{DSS} | -30 | - | - | V | $V_{GS} = 0V, I_D = -250\mu A$ | |
| Zero Gate Voltage Drain Current | IDSS | | - | -1.0 | ν μΑ | $V_{\rm GS} = -30V, V_{\rm GS} = 0V$ | |
| Gate-Source Leakage | | _ | - | ±100 | nA | $V_{\rm DS} = -50V, V_{\rm GS} = 0V$ $V_{\rm GS} = \pm 25V, V_{\rm DS} = 0V$ | |
| ON CHARACTERISTICS (Note 8) | I _{GSS} | _ | - | 100 | | $VGS = \pm 25V, VDS = 0V$ | |
| Gate Threshold Voltage | V _{GS(TH)} | -1.0 | -2.0 | -2.5 | V | $V_{DS} = V_{GS}, I_{D} = -250 \mu A$ | |
| | V GS(TH) | - | 13 | 20 | - | $V_{GS} = -10V, I_D = -8A$ | |
| Static Drain-Source On-Resistance | R _{DS(ON)} | - | 18.4 | 29 | mΩ | $V_{GS} = -5V, I_D = -5A$ | |
| Diode Forward Voltage | V _{SD} | - | -0.7 | -1.2 | V | $V_{GS} = 0V, I_S = -1A$ | |
| DYNAMIC CHARACTERISTICS (Note 9) | • 30 | | | = | | | |
| Input Capacitance | C _{iss} | - | 1931 | - | pF | | |
| Output Capacitance | C _{oss} | - | 226 | - | pF | $-V_{DS} = -15V, V_{GS} = 0V,$ -f = 1.0MHz | |
| Reverse Transfer Capacitance | C _{rss} | - | 168 | - | pF | | |
| Gate Resistance | Ra | - | 10.9 | - | Ω | $V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$ | |
| Total Gate Charge V _{GS} = -5V | Qg | - | 8.8 | - | nC | | |
| Total Gate Charge V _{GS} = -10V | Qq | - | 16.5 | - | nC | | |
| Gate-Source Charge | Q _{qs} | - | 2.6 | - | nC | V _{DS} = -15V, I _D = -10A | |
| Gate-Drain Charge | Q _{qd} | - | 3.6 | - | nC | | |
| Turn-On Delay Time | t _{D(ON)} | - | 8.2 | - | ns | 1 | |
| Turn-On Rise Time | t _R | - | 14 | - | ns | $V_{GS} = -10V, V_{DD} = -15V,$ | |
| Turn-Off Delay Time | t _{D(OFF)} | - | 65 | - | ns | $R_{GEN} = 3\Omega, I_D = -10A$ | |
| Turn-Off Fall Time | t _F | - | 31.6 | - | ns | 1 | |
| Reverse Recovery Time | t _{RR} | - | 9.3 | - | ns | | |
| Reverse Recovery Charge | Q _{RR} | - | 12.2 | - | nC | I _F = -8A, di/dt = 500A/μs | |

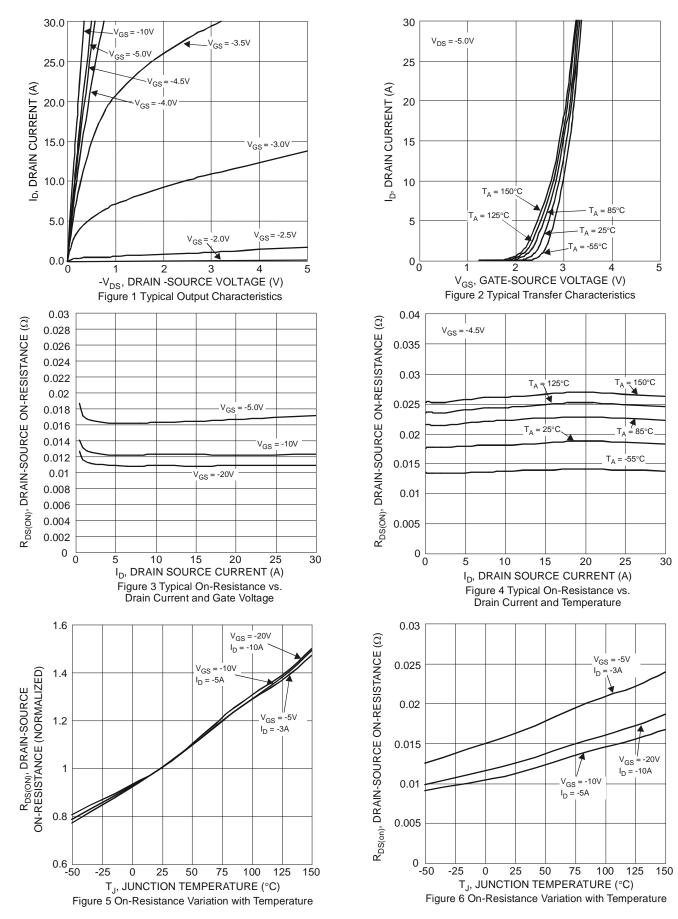
 Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate. Notes:

7. Thermal resistance from junction to soldering point (on the exposed drain pad).

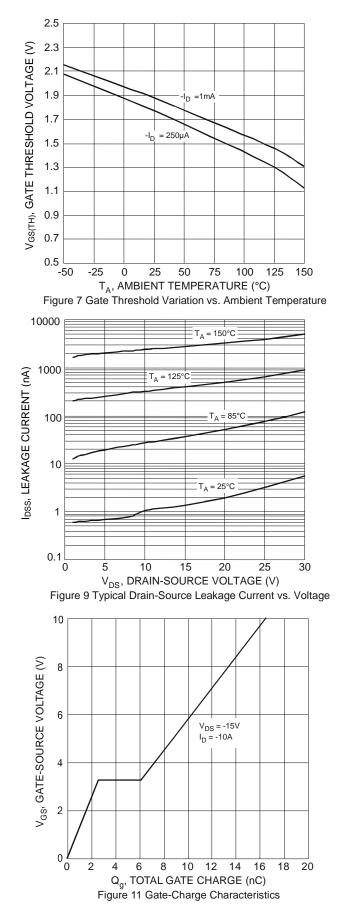
8. Short duration pulse test used to minimize self-heating effect.

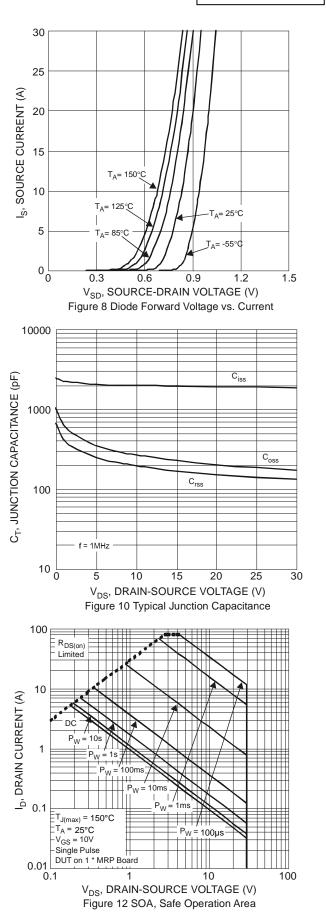
9. Guaranteed by design. Not subject to product testing.



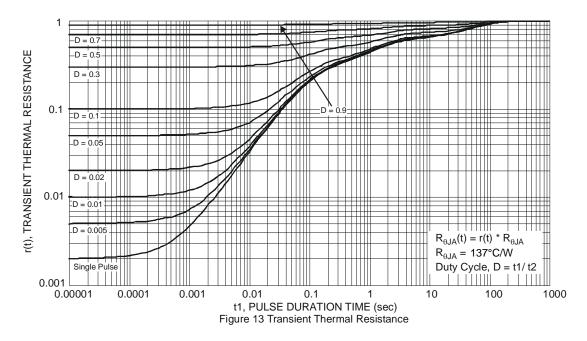








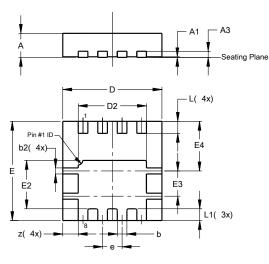






Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

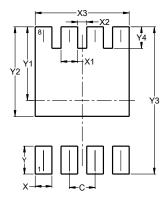


| PowerDI3333-8 | | | | | |
|----------------------|---------|------|-------|--|--|
| Dim | Min Max | | Тур | | |
| Α | 0.75 | 0.85 | 0.80 | | |
| A1 | 0.00 | 0.05 | 0.02 | | |
| A3 | - | - | 0.203 | | |
| b | 0.27 | 0.37 | 0.32 | | |
| b2 | 0.15 | 0.25 | 0.20 | | |
| D | 3.25 | 3.35 | 3.30 | | |
| D2 | 2.22 | 2.32 | 2.27 | | |
| Е | 3.25 | 3.35 | 3.30 | | |
| E2 | 1.56 | 1.66 | 1.61 | | |
| E3 | 0.79 | 0.89 | 0.84 | | |
| E4 | 1.60 | 1.70 | 1.65 | | |
| е | _ | — | 0.65 | | |
| 1 | 0.35 | 0.45 | 0.40 | | |
| L1 | _ | _ | 0.39 | | |
| z | _ | _ | 0.515 | | |
| All Dimensions in mm | | | | | |

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8



| Dimensions | Value (in mm) |
|------------|---------------|
| С | 0.650 |
| Х | 0.420 |
| X1 | 0.420 |
| X2 | 0.230 |
| Х3 | 2.370 |
| Y | 0.700 |
| Y1 | 1.850 |
| Y2 | 2.250 |
| Y3 | 3.700 |
| Y4 | 0.540 |

PowerDI3333-8



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